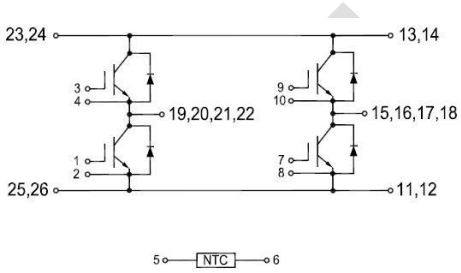
GF150HH120T6H

IGBT Module

Features：



- Non Punch Through (NPT) Technology
- Short Circuit Rated >10μs
- Low Saturation Voltage
- Low Switching Loss
- 100% RBSOA Tested(2×Ic)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement

Applications：

- SMPS、UPS
- Welding Machine
- Induction Heating

IGBT, Inverter
Maximum Rated Values

V_{CES}	Collector-Emitter Blocking Voltage	T_J=25℃	1200	V
V_{GES}	Gate-Emitter Voltage		±20	V
I_C	Continuous Collector Current	T_C=80℃	150	A
		T_C=25℃	230	A
I_{CM}	Repetitive Peak Collector Current	tp=1ms	300	A
t_{SC}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation per IGBT	T_C=25℃ T_{Jmax}=150℃	1455	W

Electrical Characteristics of IGBT

Static Characteristics

Symbol	Description	Conditions		Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=6mA, V_{CE}=V_{GE}, T_J=25℃		5.0	5.6	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=150A, V_{GE} =15V	T_J=25℃		3.20		V
			T_J=125℃		4.00		V
I_{CES}	Collector-Emitter Leakage Current	V_{GE}=0V, V_{CE}=V_{CES}, T_J=25℃				1	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=±20V, V_{CE}=0V, T_J=25℃				200	nA
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V , f =100kHz, T_J=25℃			13.39		nF
C_{oes}	Output Capacitance				1.24		nF
C_{res}	Reveres Transfer Capacitance				0.54		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	V_{CC}=600V,I_C=150A, R_{Gon}=6.8Ω,V_{GE}= ±15V, Inductive Load	T_J=25℃		639		ns
			T_J=125℃		620		
t_r	Rise Time		T_J=25℃		126		ns
			T_J=125℃		123		
$t_{d(off)}$	Turn-off Delay Time	V_{CC}=600V,I_C=150A, R_{Goff} =6.8Ω,V_{GE}= ±15V, Inductive Load	T_J=25℃		619		ns
			T_J=125℃		624		
t_f	Fall Time		T_J=25℃		150		ns
			T_J=125℃		177		
E_{on}	Turn-on Switching Loss	V_{CC}=600V,I_C=150A, R_{Gon}=6.8Ω,V_{GE}=±15V, di/dt=1040A/μs(T_J=125℃) Inductive Load	T_J=25℃		12.4		mJ
			T_J=125℃		15.4		
E_{off}	Turn-off Switching Loss	V_{CC}=600V,I_C=150A, R_{Goff} =6.8Ω,V_{GE}= ±15V, du/dt=4150V/μs(T_J=125℃) Inductive Load	T_J=25℃		7.2		mJ
			T_J=125℃		9.5		
Q_g	Total Gate Charge	V_{GE}=-15…+15V	T_J=25℃		1.81		μC
$R_{G\ Internal}$	Internal Gate Resistor		T_J=25℃		0		Ω
RBSOA	I_C=300A,V_{CC}=1050V,Vp=1200V, R_G=6.8Ω, V_{GE}=+15V to 0V, T_J=150°C			Trapezoid			
SCSOA	V_{CC}=600V, V_{GE}=15V, T_J=150℃			10			μs
$R_{θJC}$	IGBT Thermal Resistance: Junction-To-Case(per leg)					0.086	℃/W

Diode, Inverter
Maximum Rated Values

V_{RRM}	Repetitive Peak Reverse Voltage	T_J=25℃	1200	V
I_F	Diode Continuous Forward Current		150	A
I_{FM}	Diode Maximum Forward Current	tp=1ms	300	A

Electrical Characteristics of Diode

Symbol	Description	Conditions		Min	Typ	Max	Unit
V_{FM}	Forward Voltage	I_F=150A	T_J=25℃		2.40		V
			T_J=125℃		2.50		
t_{rr}	Reverse Recovery time	I_F=150A, -di$_F$/dt =1550A/μs(T_J=125℃), V_R=600V, V_{GE}=-15V	T_J=25℃		172		ns
			T_J=125℃		365		
I_{rr}	Peak Reverse Recovery Current		T_J=25℃		65.6		A
			T_J=125℃		90.6		
Q_{rr}	Reverse Recovery Charge		T_J=25℃		6.5		μC
			T_J=125℃		14.7		
E_{rec}	Reverse Recovery Energy		T_J=25℃		1.96		mJ
			T_J=125℃		5.16		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case(per leg)					0.336	℃/W

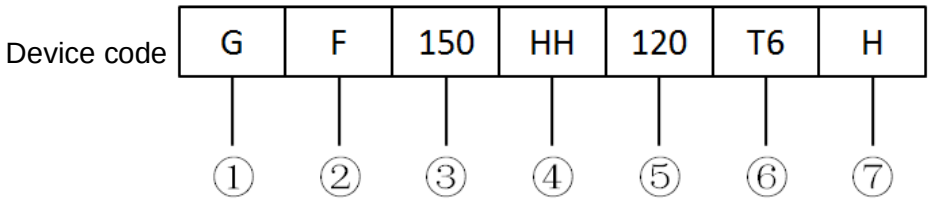
Internal NTC-Thermistor Characteristic

Symbol	Description		Min.	Typ.	Max.	Units.
R_{25}	Rated Resistance	T_C=25℃		5		kΩ
△R/R	Deviation of R100	T_C=100℃，R_{100}=481Ω	-5		5	%
P_{25}	Power Dissipation	T_C=25℃			10	mW
$B_{25/50}$	B-Value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3380		K
$B_{25/80}$	B-Value	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15K))]$		3440		K

Module

Symbol	Description		Min	Typ	Max	Unit
V_{iso}	Isolation Voltage (All Terminals Shorted)	RMS, f=50Hz, 1minute	2500			V
T_J	Maximum Junction Temperature				150	℃
T_{JOP}	Maximum Operating Junction Temperature Range		-40		+150	℃
T_{stg}	Storage Temperature		-40		+125	℃
$R_{\theta CS}$	Case-To-Sink Thermally (Conductive Grease Applied)				0.02	℃/W
M	Mounting Torque for Module Mounting	Screw M5--Mounting according to valid application note	3.0		6.0	N·m
G	Weight			300		g

Ordering Information Table



① - IGBT Module
② - Non Punch Through (NPT) Technology
③ - Rated Current (150=150A)
④ - Circuit Configuration: HH (H Bridge)
⑤ - Rated Voltage (120=1200V)
⑥ - Package Type
⑦ - Test Level (Pass the Important Reliability Test-Industrial Grade)

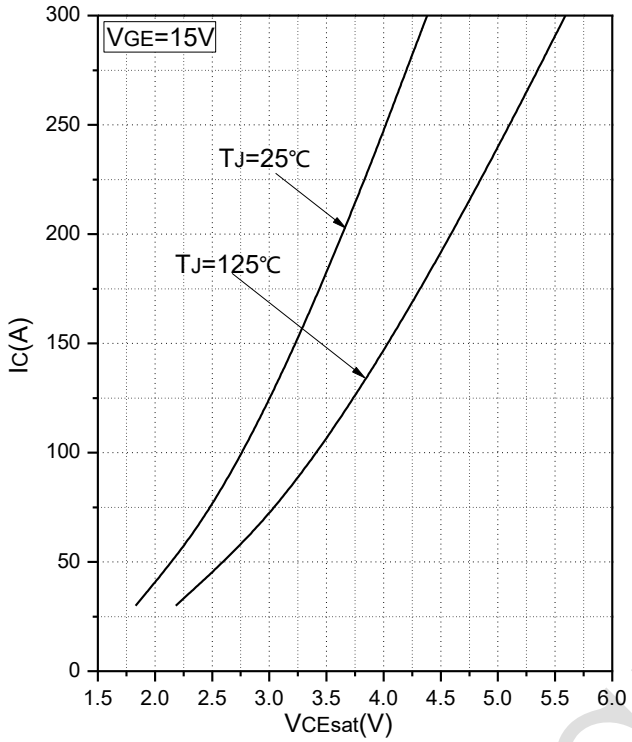


Fig.1 Typical Saturation Voltage Characteristics

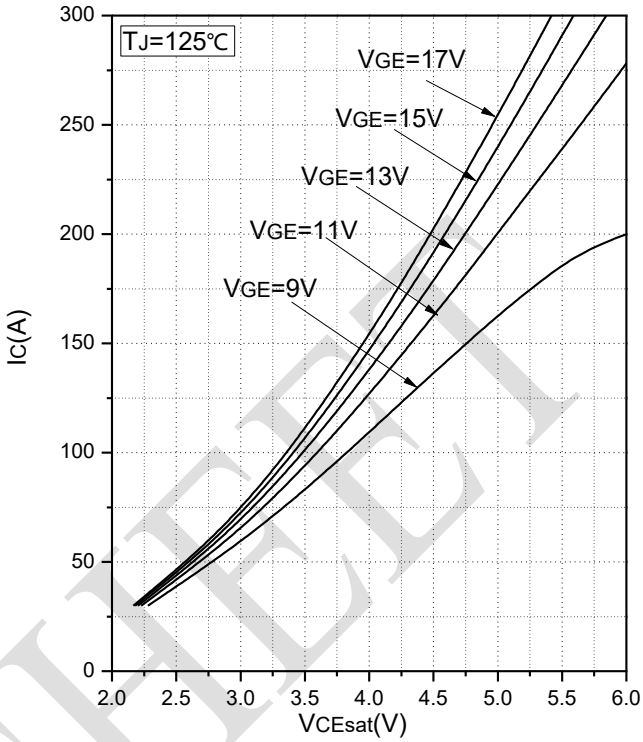


Fig.2 Typical Output Characteristics

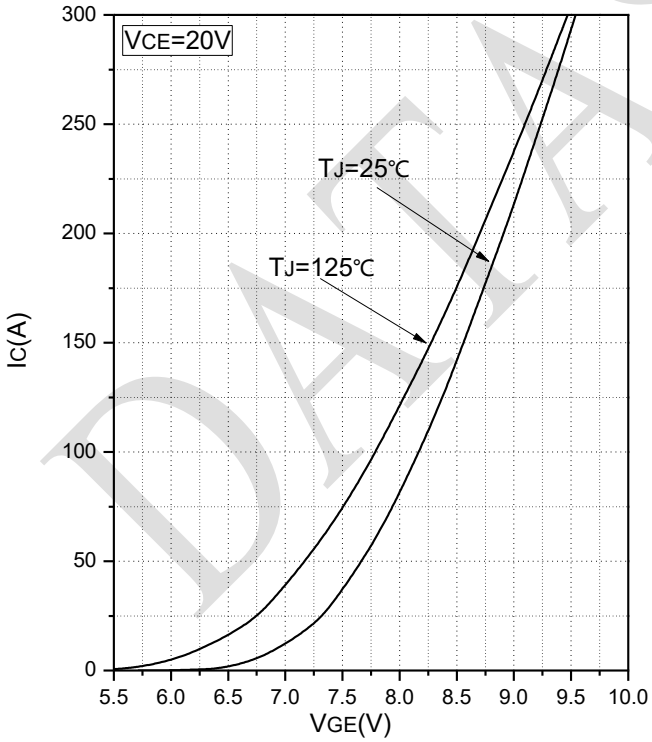


Fig.3 Transfer Characteristic

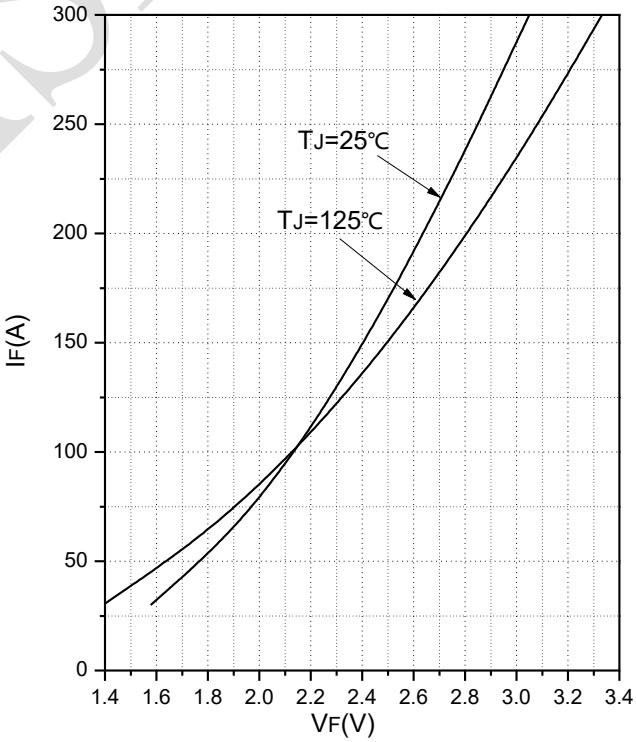


Fig.4 Forward Characteristics of Diode

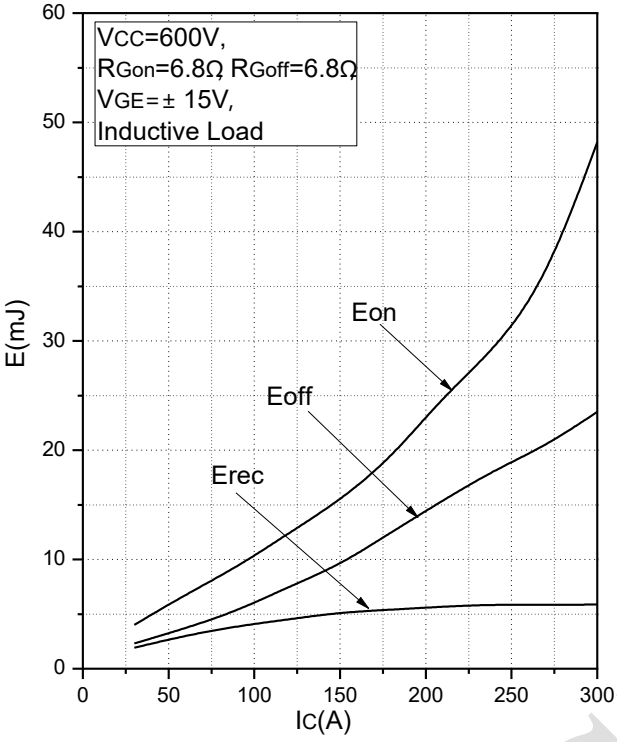


Fig.5 Typical Switching Loss vs. Collector Current

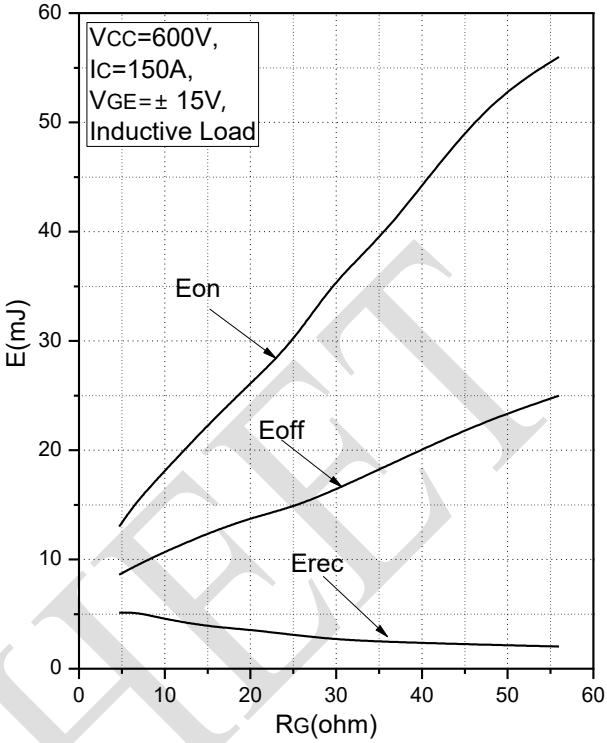


Fig.6 Typical Switching Loss vs. Gate Resistance

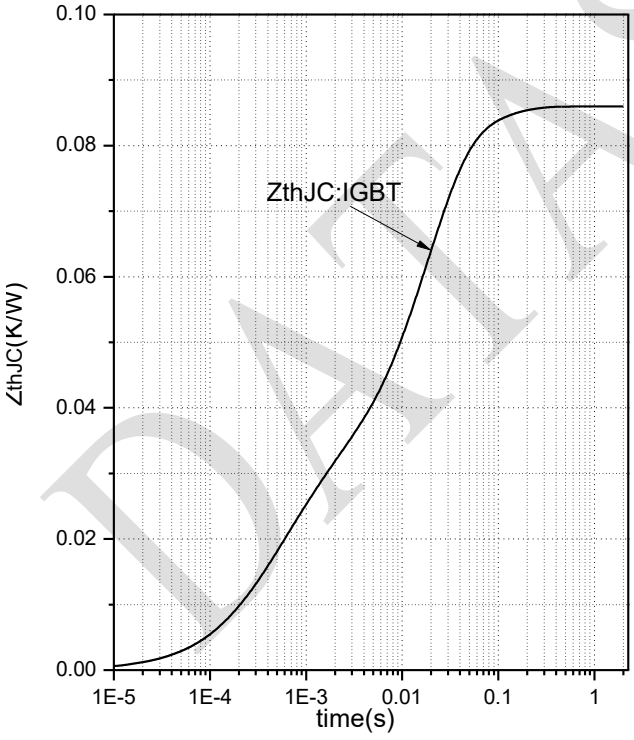


Fig.7 Transient Thermal Impedance (IGBT)

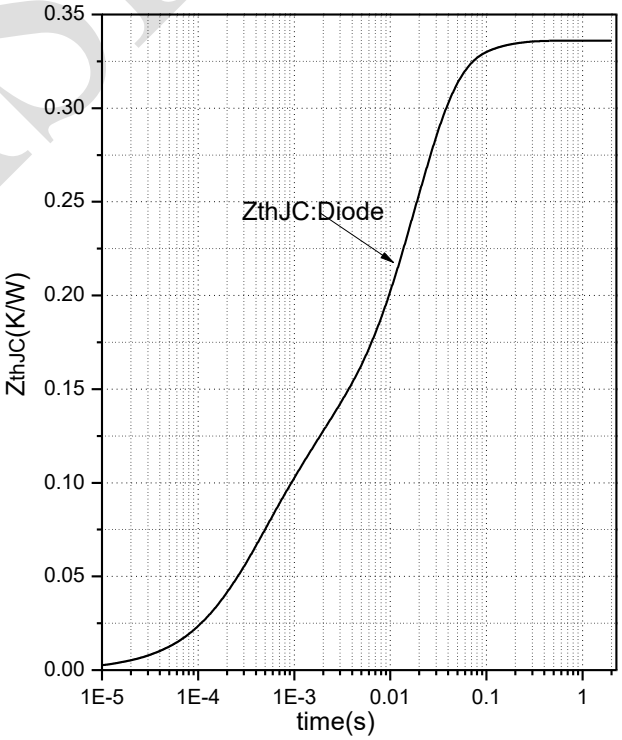


Fig.8 Transient Thermal Impedance (Diode)

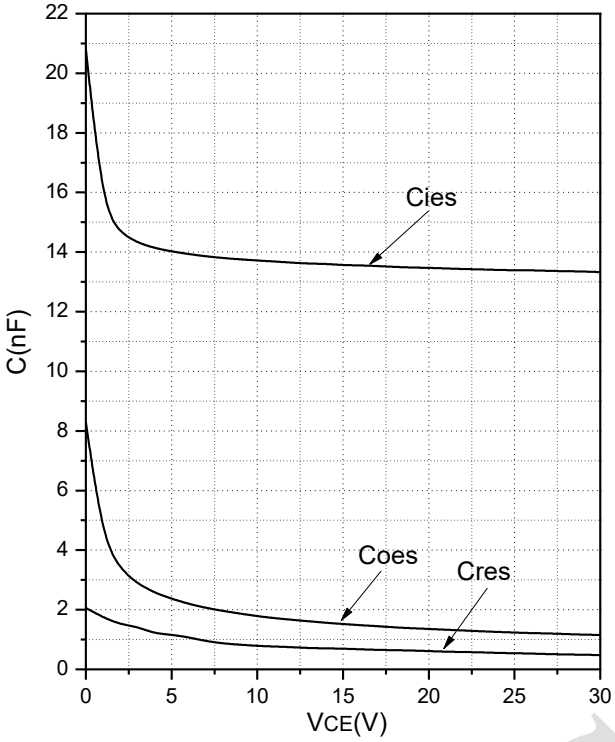


Fig.9 Capacitance Characteristics

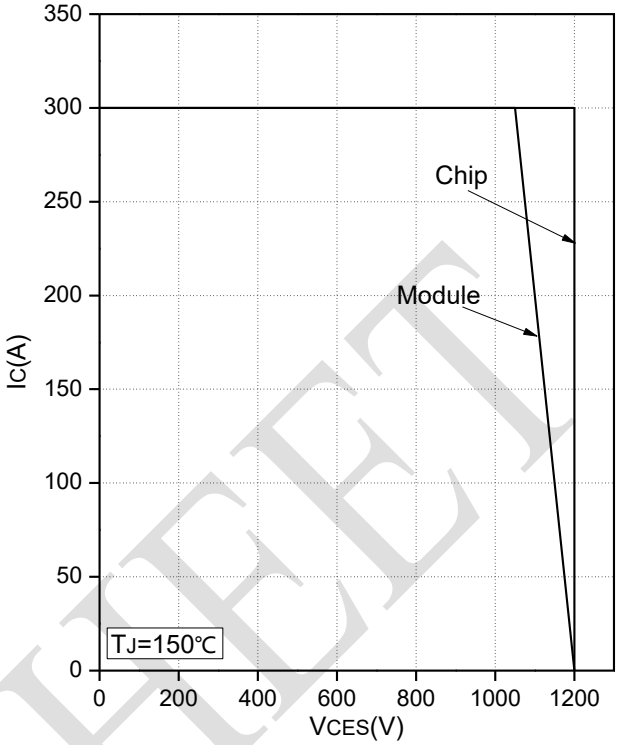


Fig.10 Reverse Bias Safe Operation Area (RBSOA)

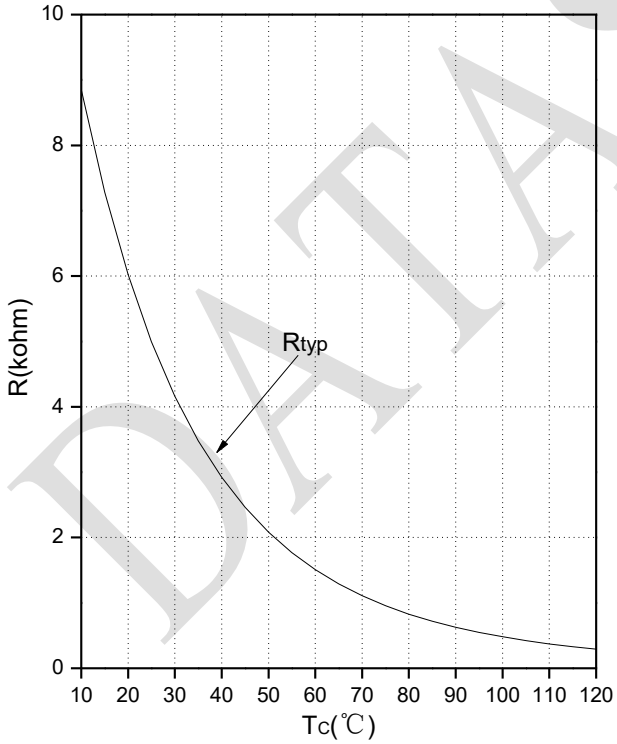
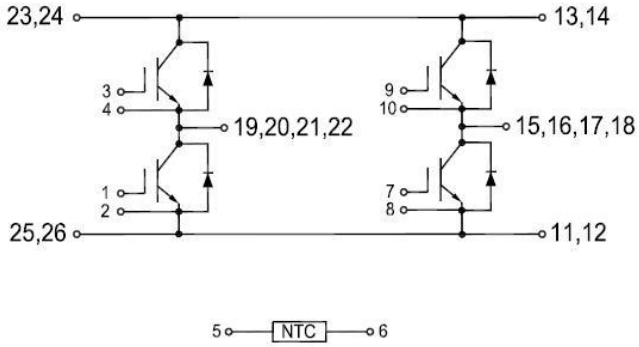
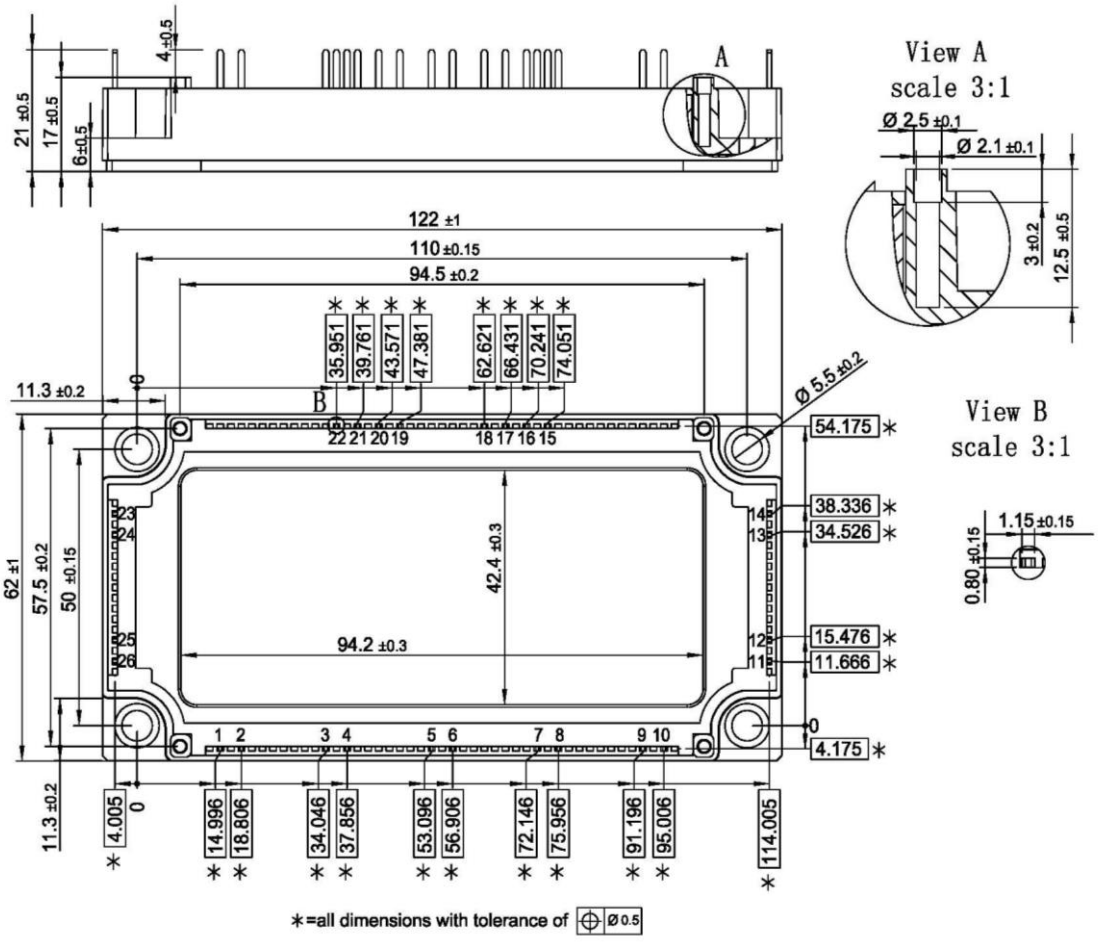


Fig.11 NTC Temperature Characteristics

Internal Circuit



Package Outline (Unit: mm):



Date	Revision	Notes
07/07/2022	A	Final Version

Announcement

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